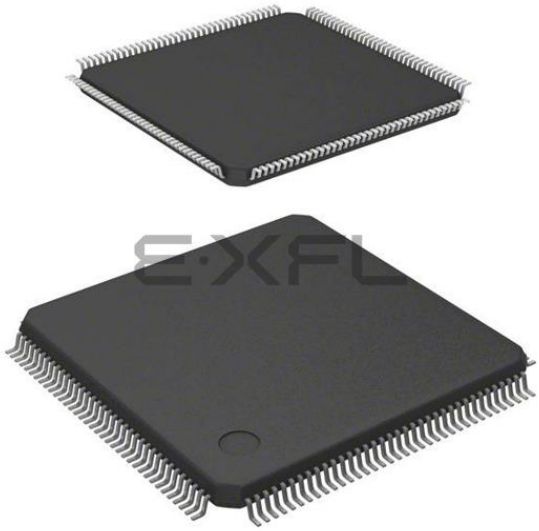

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, DCMI, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	114
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f407zgt6tr

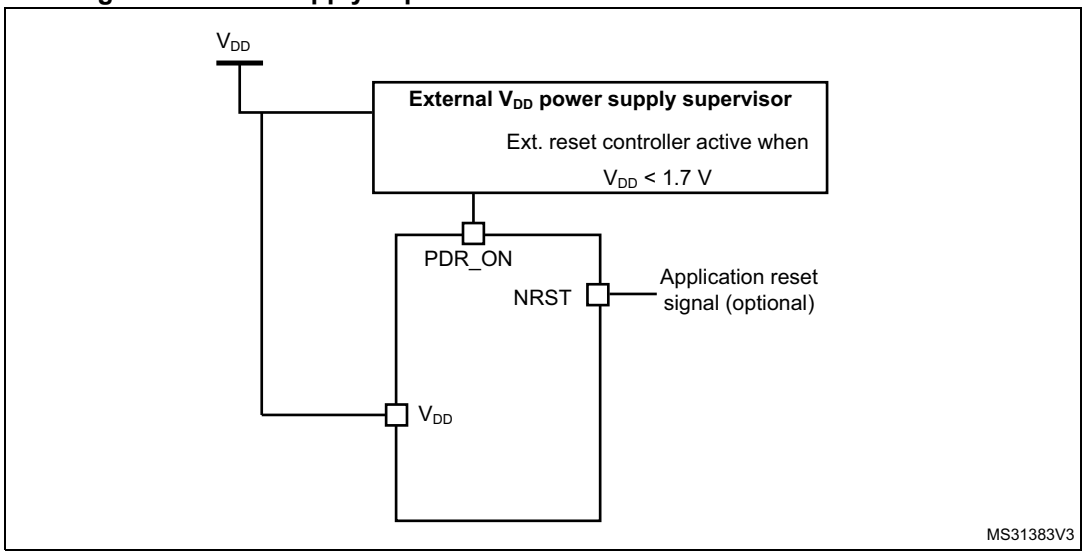
The device also features an embedded programmable voltage detector (PVD) that monitors the V_{DD}/V_{DDA} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD}/V_{DDA} drops below the V_{PVD} threshold and/or when V_{DD}/V_{DDA} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

Internal reset OFF

This feature is available only on packages featuring the PDR_ON pin. The internal power-on reset (POR) / power-down reset (PDR) circuitry is disabled with the PDR_ON pin.

An external power supply supervisor should monitor V_{DD} and should maintain the device in reset mode as long as V_{DD} is below a specified threshold. PDR_ON should be connected to this external power supply supervisor. Refer to *Figure 7: Power supply supervisor interconnection with internal reset OFF*.

Figure 7. Power supply supervisor interconnection with internal reset OFF



1. PDR = 1.7 V for reduce temperature range; PDR = 1.8 V for all temperature range.

The V_{DD} specified threshold, below which the device must be maintained under reset, is 1.8 V (see *Figure 7*). This supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range.

A comprehensive set of power-saving mode allows to design low-power applications.

When the internal reset is OFF, the following integrated features are no more supported:

- The integrated power-on reset (POR) / power-down reset (PDR) circuitry is disabled
- The brownout reset (BOR) circuitry is disabled
- The embedded programmable voltage detector (PVD) is disabled
- V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}

All packages, except for the LQFP64 and LQFP100, allow to disable the internal reset through the PDR_ON signal.

Standby mode, the SRAM and register contents are lost except for registers in the backup domain and the backup SRAM when selected.

The device exits the Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm / wakeup / tamper /time stamp event occurs.

The standby mode is not supported when the embedded voltage regulator is bypassed and the V_{12} domain is controlled by an external power.

2.2.20 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery, an external supercapacitor, or from V_{DD} when no external battery and an external supercapacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When PDR_ON pin is not connected to V_{DD} (internal reset OFF), the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}.

2.2.21 Timers and watchdogs

The STM32F405xx and STM32F407xx devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

Table 4 compares the features of the advanced-control, general-purpose and basic timers.

Table 4. Timer feature comparison

Timer type	Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/ compare channels	Complemen-tary output	Max interface clock (MHz)	Max timer clock (MHz)
Advanced -control	TIM1, TIM8	16-bit	Up, Down, Up/down	Any integer between 1 and 65536	Yes	4	Yes	84	168

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)[1]	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	-	-	49	R6	59	PF11	I/O	FT	-	DCMI_D12/ EVENTOUT	-
-	-	-	50	P6	60	PF12	I/O	FT	-	FSMC_A6/ EVENTOUT	-
-	-	-	51	M8	61	V_{SS}	S	-	-	-	-
-	-	-	52	N8	62	V_{DD}	S	-	-	-	-
-	-	-	53	N6	63	PF13	I/O	FT	-	FSMC_A7/ EVENTOUT	-
-	-	-	54	R7	64	PF14	I/O	FT	-	FSMC_A8/ EVENTOUT	-
-	-	-	55	P7	65	PF15	I/O	FT	-	FSMC_A9/ EVENTOUT	-
-	-	-	56	N7	66	PG0	I/O	FT	-	FSMC_A10/ EVENTOUT	-
-	-	-	57	M7	67	PG1	I/O	FT	-	FSMC_A11/ EVENTOUT	-
-	G6	38	58	R8	68	PE7	I/O	FT	-	FSMC_D4/TIM1_ETR/ EVENTOUT	-
-	H6	39	59	P8	69	PE8	I/O	FT	-	FSMC_D5/ TIM1_CH1N/ EVENTOUT	-
-	J6	40	60	P9	70	PE9	I/O	FT	-	FSMC_D6/TIM1_CH1/ EVENTOUT	-
-	-	-	61	M9	71	V_{SS}	S	-	-	-	-
-	-	-	62	N9	72	V_{DD}	S	-	-	-	-
-	F6	41	63	R9	73	PE10	I/O	FT	-	FSMC_D7/TIM1_CH2N/ EVENTOUT	-
-	J5	42	64	P10	74	PE11	I/O	FT	-	FSMC_D8/TIM1_CH2/ EVENTOUT	-
-	H5	43	65	R10	75	PE12	I/O	FT	-	FSMC_D9/TIM1_CH3N/ EVENTOUT	-
-	G5	44	66	N11	76	PE13	I/O	FT	-	FSMC_D10/TIM1_CH3/ EVENTOUT	-
-	F5	45	67	P11	77	PE14	I/O	FT	-	FSMC_D11/TIM1_CH4/ EVENTOUT	-
-	G4	46	68	R11	78	PE15	I/O	FT	-	FSMC_D12/TIM1_BKIN/ EVENTOUT	-

Table 10. register boundary addresses (continued)

Bus	Boundary address	Peripheral
AHB1	0x4004 0000 - 0x4007 FFFF	USB OTG HS
	0x4002 9400 - 0x4003 FFFF	Reserved
	0x4002 9000 - 0x4002 93FF	ETHERNET MAC
	0x4002 8C00 - 0x4002 8FFF	
	0x4002 8800 - 0x4002 8BFF	
	0x4002 8400 - 0x4002 87FF	
	0x4002 8000 - 0x4002 83FF	
	0x4002 6800 - 0x4002 7FFF	Reserved
	0x4002 6400 - 0x4002 67FF	DMA2
	0x4002 6000 - 0x4002 63FF	DMA1
	0x4002 5000 - 0x4002 5FFF	Reserved
	0x4002 4000 - 0x4002 4FFF	BKPSRAM
	0x4002 3C00 - 0x4002 3FFF	Flash interface register
	0x4002 3800 - 0x4002 3BFF	RCC
	0x4002 3400 - 0x4002 37FF	Reserved
	0x4002 3000 - 0x4002 33FF	CRC
	0x4002 2400 - 0x4002 2FFF	Reserved
	0x4002 2000 - 0x4002 23FF	GPIOI
	0x4002 1C00 - 0x4002 1FFF	GPIOH
	0x4002 1800 - 0x4002 1BFF	GPIOG
	0x4002 1400 - 0x4002 17FF	GPIOF
	0x4002 1000 - 0x4002 13FF	GPIOE
	0x4002 0C00 - 0x4002 0FFF	GPIOD
	0x4002 0800 - 0x4002 0BFF	GPIOC
	0x4002 0400 - 0x4002 07FF	GPIOB
	0x4002 0000 - 0x4002 03FF	GPIOA
	0x4001 5800- 0x4001 FFFF	Reserved

Table 14. General operating conditions (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{12}	Regulator ON: 1.2 V internal voltage on V_{CAP_1}/V_{CAP_2} pins	VOS bit in PWR_CR register = 0(1) Max frequency 144MHz	1.08	1.14	1.20	V
		VOS bit in PWR_CR register= 1 Max frequency 168MHz	1.20	1.26	1.32	V
	Regulator OFF: 1.2 V external voltage must be supplied from external regulator on V_{CAP_1}/V_{CAP_2} pins	Max frequency 144MHz	1.10	1.14	1.20	V
		Max frequency 168MHz	1.20	1.26	1.30	V
V_{IN}	Input voltage on RST and FT pins(6)	2 V ≤ V_{DD} ≤ 3.6 V	–0.3	-	5.5	V
		V_{DD} ≤ 2 V	–0.3	-	5.2	
	Input voltage on TTa pins	-	–0.3	-	V_{DDA}+ 0.3	
	Input voltage on B pin	-	-	-	5.5	
P_D	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(7)	LQFP64	-	-	435	mW
		LQFP100	-	-	465	
		LQFP144	-	-	500	
		LQFP176	-	-	526	
		UFBGA176	-	-	513	
		WLCSP90	-	-	543	
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	-	85	°C
		Low-power dissipation(8)	–40	-	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	-	105	°C
		Low-power dissipation(8)	–40	-	125	
T_J	Junction temperature range	6 suffix version	–40	-	105	°C
		7 suffix version	–40	-	125	

1. The average expected gain in power consumption when VOS = 0 compared to VOS = 1 is around 10% for the whole temperature range, when the system clock frequency is between 30 and 144 MHz.
2. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).
3. When the ADC is used, refer to *Table 67: ADC characteristics*.
4. If V_{REF+} pin is present, it must respect the following condition: V_{DDA}-V_{REF+} < 1.2 V.
5. It is recommended to power V_{DD} and V_{DDA} from the same source. A maximum difference of 300 mV between V_{DD} and V_{DDA} can be tolerated during power-up and power-down operation.
6. To sustain a voltage higher than V_{DD}+0.3, the internal pull-up and pull-down resistors must be disabled.
7. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax}.
8. In low-power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax}.

Table 28. Peripheral current consumption (continued)

Peripheral		I_{DD}(Typ)(1)		Unit
		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	
AHB2 (up to 168 MHz)	OTG_FS	26.45	26.67	µA/MHz
	DCMI	5.87	5.35	
	RNG	1.50	1.67	
AHB3 (up to 168 MHz)	FSMC	12.46	11.31	µA/MHz
Bus matrix(2)		13.10	11.81	µA/MHz
APB1 (up to 42 MHz)	TIM2	16.71	16.50	µA/MHz
	TIM3	12.33	11.94	
	TIM4	13.45	12.92	
	TIM5	17.14	16.58	
	TIM6	2.43	3.06	
	TIM7	2.43	2.22	
	TIM12	6.62	6.83	
	TIM13	5.05	5.47	
	TIM14	5.26	5.61	
	PWR	1.00	0.56	
	USART2	2.69	2.78	
	USART3	2.74	2.78	
	UART4	3.24	3.33	
	UART5	2.69	2.78	
	I2C1	2.67	2.50	
	I2C2	2.83	2.78	
	I2C3	2.81	2.78	
	SPI2	2.43	2.22	
	SPI3	2.43	2.22	
	I2S2(3)	2.43	2.22	
	I2S3(3)	2.26	2.22	
	CAN1	5.12	5.56	
	CAN2	4.81	5.28	
	DAC(4)	1.67	1.67	
	WWDG	1.00	0.83	

Table 29. Low-power mode wakeup timings

Symbol	Parameter	Min(1)	Typ(1)	Max(1)	Unit
$t_{WUSLEEP}$(2)	Wakeup from Sleep mode	-	5	-	CPU clock cycle
t_{WUSTOP}(2)	Wakeup from Stop mode (regulator in Run mode and Flash memory in Stop mode)	-	13	-	µs
	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Stop mode)	-	17	40	
	Wakeup from Stop mode (regulator in Run mode and Flash memory in Deep power-down mode)	-	105	-	
	Wakeup from Stop mode (regulator in low-power mode and Flash memory in Deep power-down mode)	-	110	-	
$t_{WUSTDBY}$(2)(3)	Wakeup from Standby mode	260	375	480	µs

1. Guaranteed by characterization.
2. The wakeup times are measured from the wakeup event to the point in which the application code reads the first instruction.
3. $t_{WUSTDBY}$ minimum and maximum values are given at 105 °C and –45 °C, respectively.

5.3.8 External clock source characteristics

High-speed external user clock generated from an external source

The characteristics given in *Table 30* result from tests performed using an high-speed external clock source, and under ambient temperature and supply voltage conditions summarized in *Table 14*.

Table 30. High-speed external user clock characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HSE_ext}	External user clock source frequency(1)	-	1	-	50	MHz
V_{HSEH}	OSC_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{HSEL}	OSC_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(HSE)}$ $t_{w(HSE)}$	OSC_IN high or low time(1)		5	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time(1)		-	-	10	
$C_{in(HSE)}$	OSC_IN input capacitance(1)	-	-	5	-	pF
$DuCy_{(HSE)}$	Duty cycle	-	45	-	55	%
I_L	OSC_IN Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1	µA

1. Guaranteed by design.

Table 41. Flash memory programming with V_{PP}

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{prog}	Double word programming	T_A = 0 to +40 °C V_{DD} = 3.3 V V_{PP} = 8.5 V	-	16	100(2)	µs
$t_{ERASE16KB}$	Sector (16 KB) erase time		-	230	-	ms
$t_{ERASE64KB}$	Sector (64 KB) erase time		-	490	-	
$t_{ERASE128KB}$	Sector (128 KB) erase time		-	875	-	
t_{ME}	Mass erase time		-	6.9	-	s
V_{prog}	Programming voltage	-	2.7	-	3.6	V
V_{PP}	V_{PP} voltage range	-	7	-	9	V
I_{PP}	Minimum current sunk on the V_{PP} pin	-	10	-	-	mA
t_{VPP}(3)	Cumulative time during which V_{PP} is applied	-	-	-	1	hour

1. Guaranteed by design.
2. The maximum programming time is measured after 100K erase operations.
3. V_{PP} should only be connected during programming/erasing.

Table 42. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min(1)	
N_{END}	Endurance	T_A = –40 to +85 °C (6 suffix versions) T_A = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Guaranteed by characterization.
2. Cycling performed over the whole temperature range.

5.3.13 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

Table 53. Characteristics of TIMx connected to the APB2 domain(1)

Symbol	Parameter	Conditions	Min	Max	Unit
$t_{res(TIM)}$	Timer resolution time	AHB/APB2 prescaler distinct from 1, $f_{TIMxCLK}$ = 168 MHz	1	-	$t_{TIMxCLK}$
			5.95	-	ns
		AHB/APB2 prescaler = 1, $f_{TIMxCLK}$ = 84 MHz	1	-	$t_{TIMxCLK}$
			11.9	-	ns
f_{EXT}	Timer external clock frequency on CH1 to CH4	$f_{TIMxCLK}$ = 168 MHz APB2 = 84 MHz	0	$f_{TIMxCLK}/2$	MHz
			0	84	MHz
Res_{TIM}	Timer resolution		-	16	bit
$t_{COUNTER}$	16-bit counter clock period when internal clock is selected		1	65536	$t_{TIMxCLK}$
t_{MAX_COUNT}	Maximum possible count		-	32768	$t_{TIMxCLK}$

1. TIMx is used as a general term to refer to the TIM1, TIM8, TIM9, TIM10, and TIM11 timers.

5.3.19 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s.

The I²C timings requirements are guaranteed by design when the I2C peripheral is properly configured (refer to RM0090 reference manual).

The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present. Refer to *Section 5.3.16: I/O port characteristics* for more details on the I²C I/O characteristics.

All I²C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Table 54. I2C analog filter characteristics(1)

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50(2)	260(3)	ns

1. Guaranteed by design.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

Table 67. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{lat}(4)	Injection trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.100	µs
			-	-	3(7)	$1/f_{ADC}$
t_{latr}(4)	Regular trigger conversion latency	f_{ADC} = 30 MHz	-	-	0.067	µs
			-	-	2(7)	$1/f_{ADC}$
t_S(4)	Sampling time	f_{ADC} = 30 MHz	0.100	-	16	µs
		-	3	-	480	$1/f_{ADC}$
t_{STAB}(4)	Power-up time	-	-	2	3	µs
t_{CONV}(4)	Total conversion time (including sampling time)	f_{ADC} = 30 MHz 12-bit resolution	0.50	-	16.40	µs
		f_{ADC} = 30 MHz 10-bit resolution	0.43	-	16.34	µs
		f_{ADC} = 30 MHz 8-bit resolution	0.37	-	16.27	µs
		f_{ADC} = 30 MHz 6-bit resolution	0.30	-	16.20	µs
		9 to 492 (t_S for sampling +n-bit resolution for successive approximation)				$1/f_{ADC}$
f_S(4)	Sampling rate (f_{ADC} = 30 MHz, and t_S = 3 ADC cycles)	12-bit resolution Single ADC	-	-	2	Msps
		12-bit resolution Interleave Dual ADC mode	-	-	3.75	Msps
		12-bit resolution Interleave Triple ADC mode	-	-	6	Msps
I_{VREF+}(4)	ADC V_{REF} DC current consumption in conversion mode	-	-	300	500	µA
I_{VDDA}(4)	ADC V_{DDA} DC current consumption in conversion mode	-	-	1.6	1.8	mA

1. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).
2. It is recommended to maintain the voltage difference between V_{REF+} and V_{DDA} below 1.8 V.
3. V_{DDA} -V_{REF+} < 1.2 V.
4. Guaranteed by characterization.
5. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA}.
6. R_{ADC} maximum value is given for V_{DD}=1.8 V, and minimum value for V_{DD}=3.3 V.
7. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 67*.

Table 74. DAC characteristics (continued)

Symbol	Parameter	Min	Typ	Max	Unit	Comments
Offset(4)	Offset error (difference between measured value at Code (0x800) and the ideal value = V_{REF+}/2)	-	-	±10	mV	Given for the DAC in 12-bit configuration
		-	-	±3	LSB	Given for the DAC in 10-bit at V_{REF+} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V_{REF+} = 3.6 V
Gain error(4)	Gain error	-	-	±0.5	%	Given for the DAC in 12-bit configuration
$t_{SETTLING}$(4)	Settling time (full scale: for a 10-bit input code transition between the lowest and the highest input codes when DAC_OUT reaches final value ±4LSB	-	3	6	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
THD(4)	Total Harmonic Distortion Buffer ON	-	-	-	dB	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
Update rate(2)	Max frequency for a correct DAC_OUT change when small variation in the input code (from code i to i+1LSB)	-	-	1	MS/s	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ
t_{WAKEUP}(4)	Wakeup time from off state (Setting the ENx bit in the DAC Control register)	-	6.5	10	µs	$C_{LOAD} \leq 50$ pF, $R_{LOAD} \geq 5$ kΩ input code between lowest and highest possible ones.
PSRR+ (2)	Power supply rejection ratio (to V_{DDA}) (static DC measurement)	-	–67	–40	dB	No R_{LOAD}, C_{LOAD} = 50 pF

1. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).
2. Guaranteed by design.
3. The quiescent mode corresponds to a state where the DAC maintains a stable output level to ensure that no dynamic consumption occurs.
4. Guaranteed by characterization.

2. Guaranteed by characterization.

Synchronous waveforms and timings

Figure 58 through *Figure 61* represent synchronous waveforms and *Table 80* through *Table 82* provide the corresponding timings. The results shown in these tables are obtained with the following FSMC configuration:

- BurstAccessMode = FSMC_BurstAccessMode_Enable;
- MemoryType = FSMC_MemoryType_CRAM;
- WriteBurst = FSMC_WriteBurst_Enable;
- CLKDivision = 1; (0 is not supported, see the STM32F40xxx/41xxx reference manual)
- DataLatency = 1 for NOR Flash; DataLatency = 0 for PSRAM

In all timing tables, the T_{HCLK} is the HCLK clock period (with maximum FSMC_CLK = 60 MHz).

Figure 58. Synchronous multiplexed NOR/PSRAM read timings

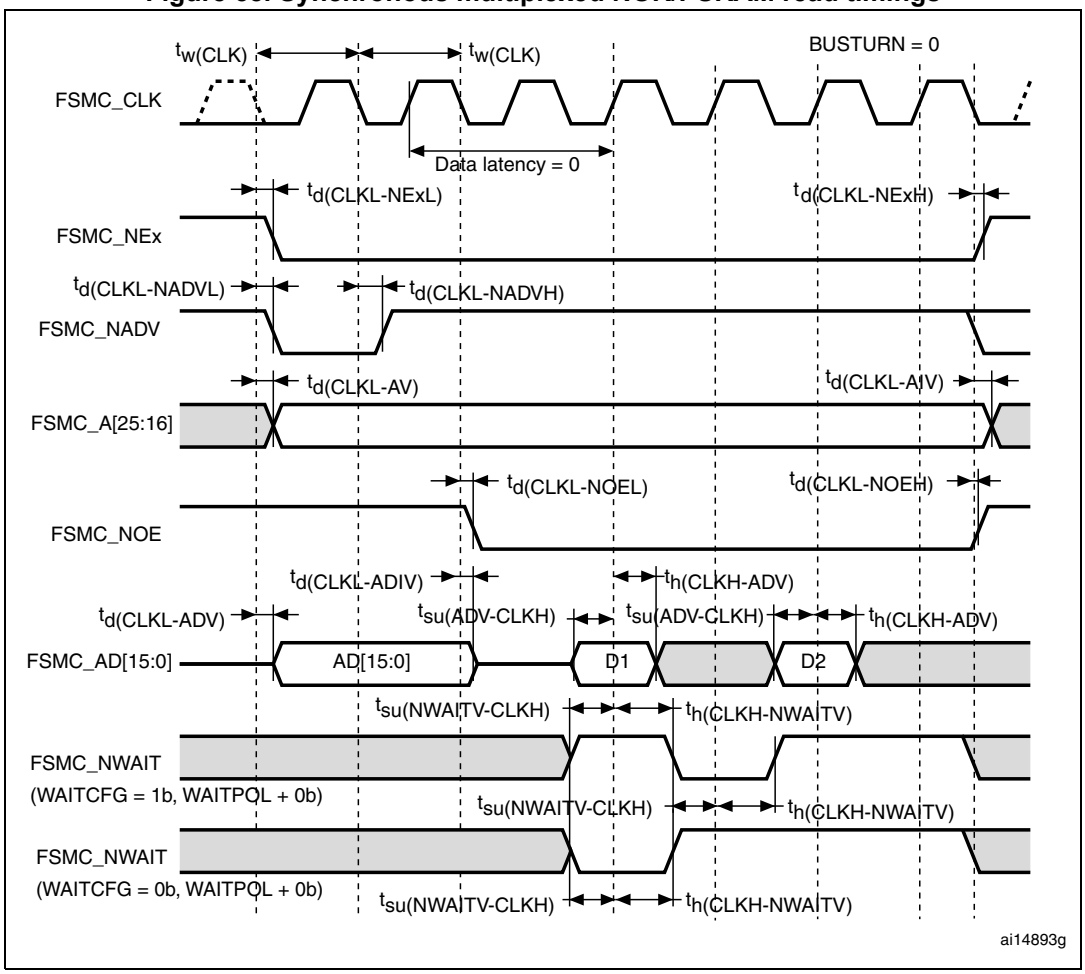


Table 90. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.540	0.570	0.600	0.0213	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	-	0.380	-	-	0.0150	-
A3[2]	-	0.025	-	-	0.0010	-
b[3]	0.240	0.270	0.300	0.0094	0.0106	0.0118
D	4.188	4.223	4.258	0.1649	0.1663	0.1676
E	3.934	3.969	4.004	0.1549	0.1563	0.1576
e	-	0.400	-	-	0.0157	-
e1	-	3.600	-	-	0.1417	-
e2	-	3.200	-	-	0.1260	-
F	-	0.3115	-	-	0.0123	-
G	-	0.3845	-	-	0.0151	-
aaa	-	0.100	-	-	0.0039	-
bbb	-	0.100	-	-	0.0039	-
ccc	-	0.100	-	-	0.0039	-
ddd	-	0.050	-	-	0.0020	-
eee	-	0.050	-	-	0.0020	-

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Back side coating.
3. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Figure 76. WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale recommended footprint

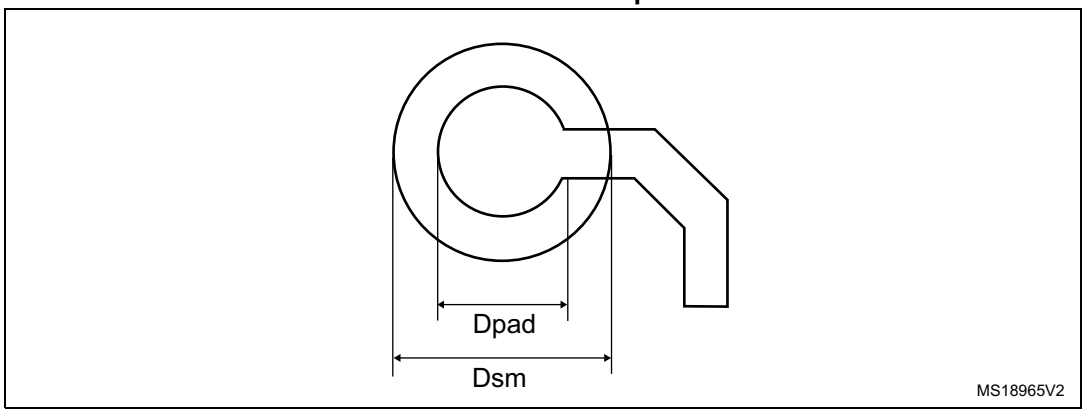


Table 91. WLCSP90 recommended PCB design rules

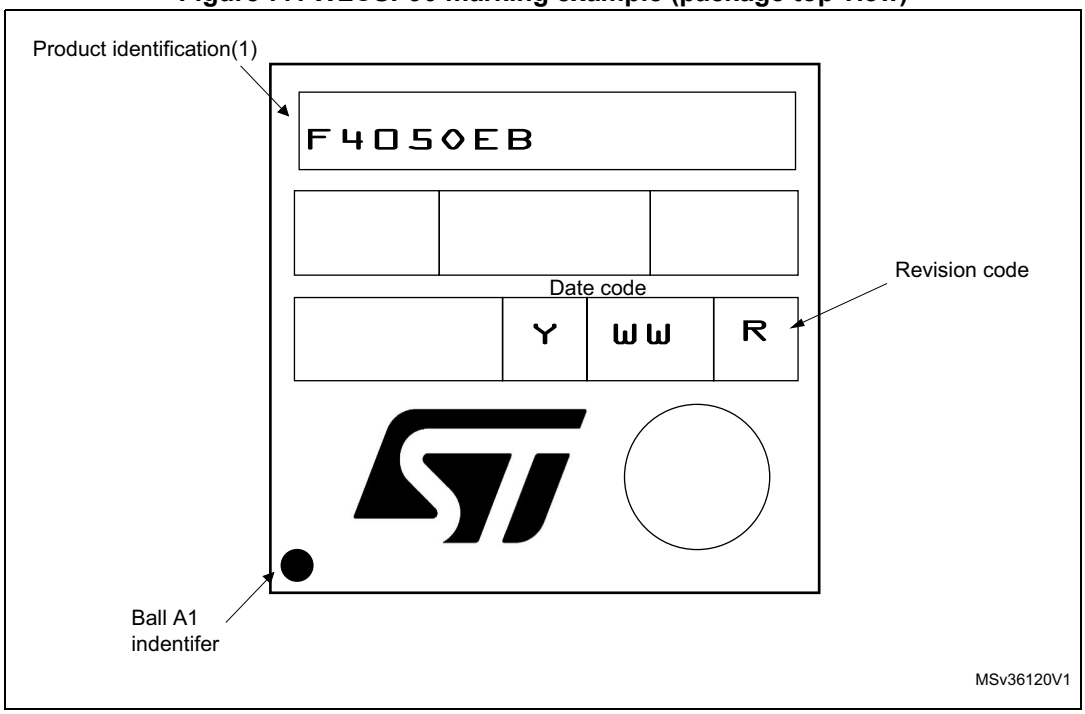
Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 µm min. (for 260 µm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed

Device marking for WLCSP90

The following figure gives an example of topside marking and ball A1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 77. WLCSP90 marking example (package top view)



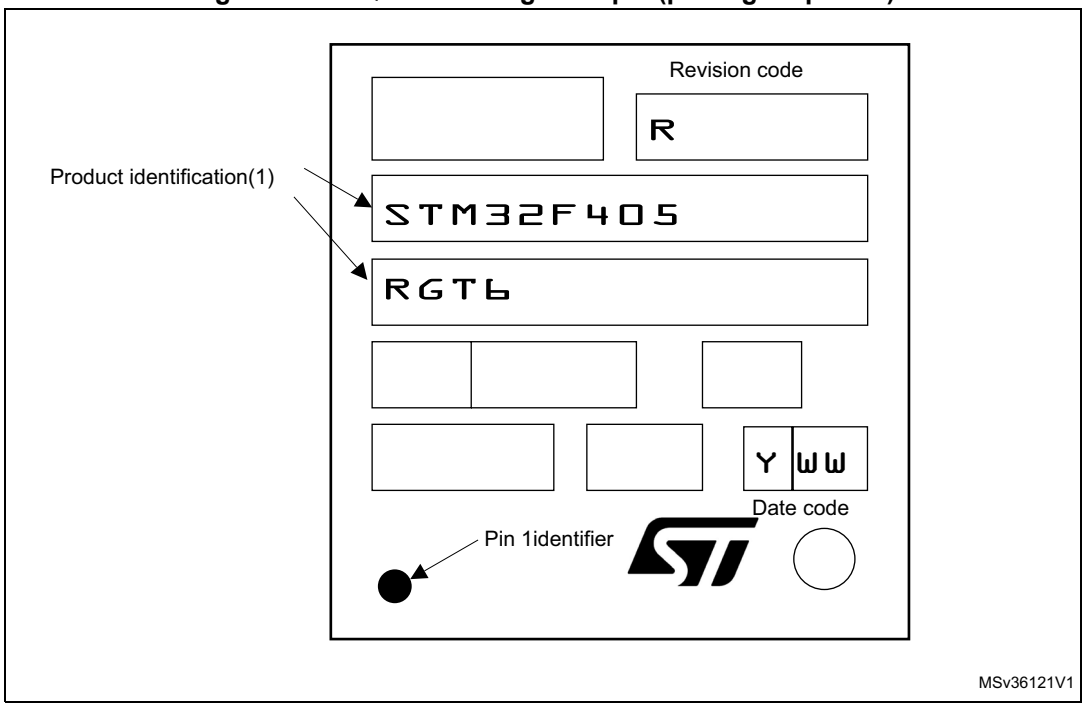
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking for LQFP64

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 80. LPQF64 marking example (package top view)



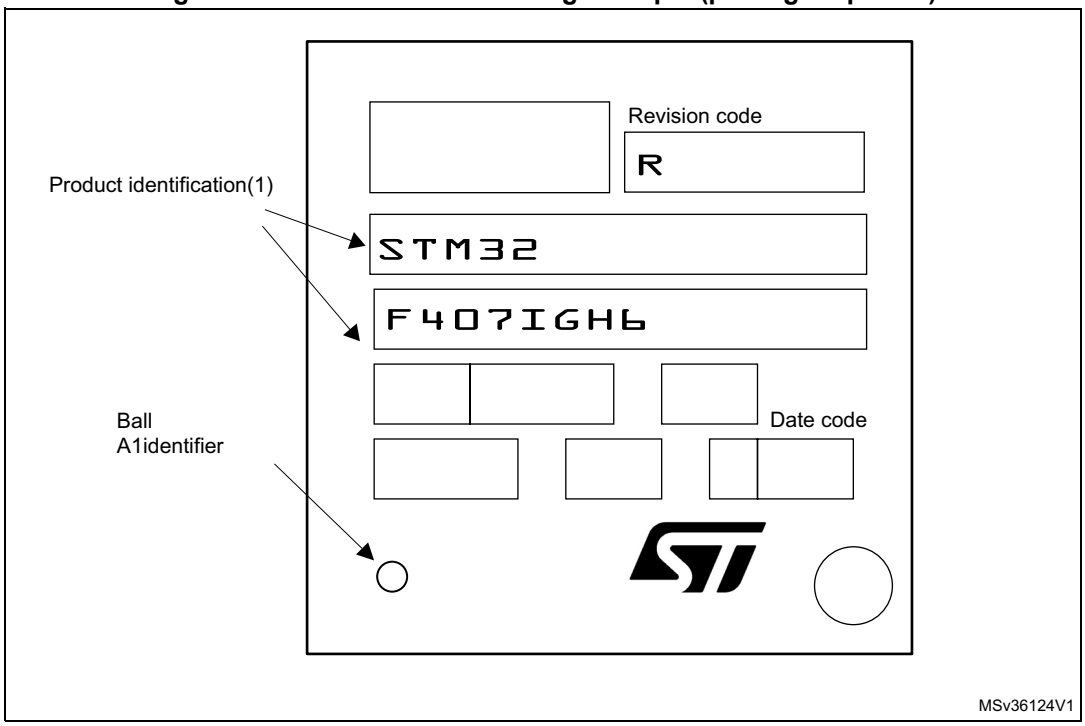
1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Device marking for UFBGA176+25

The following figure gives an example of topside marking and ball A 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 89. UFBGA176+25 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

6.7 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max x Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 98. Package thermal characteristics

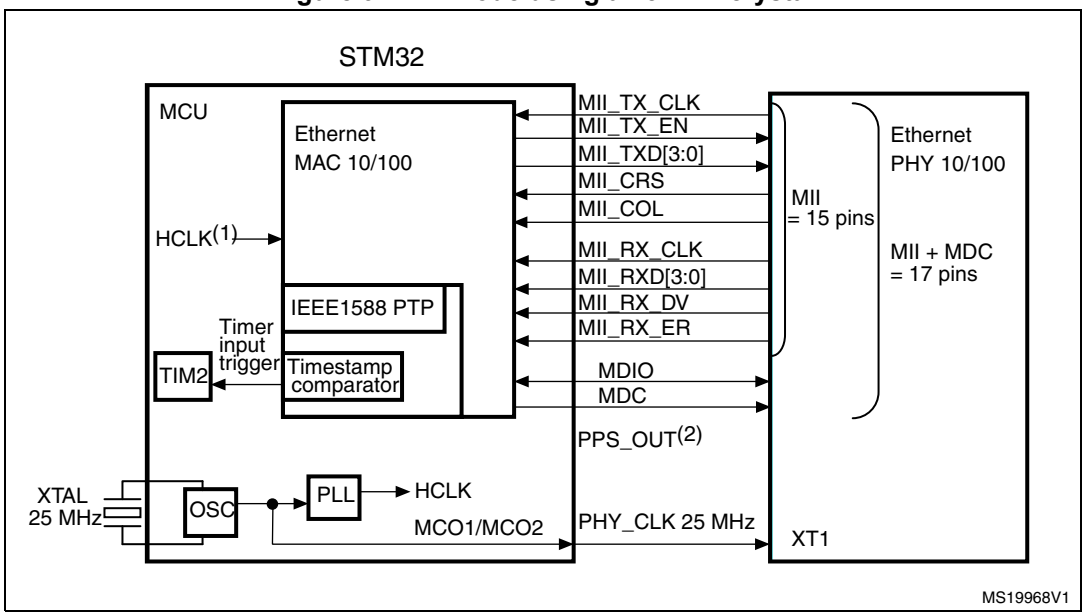
Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP64 - 10 × 10 mm / 0.5 mm pitch	46	°C/W
	Thermal resistance junction-ambient LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient UFBGA176 - 10× 10 mm / 0.65 mm pitch	39	
	Thermal resistance junction-ambient WLCSP90 - 0.400 mm pitch	38.1	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.

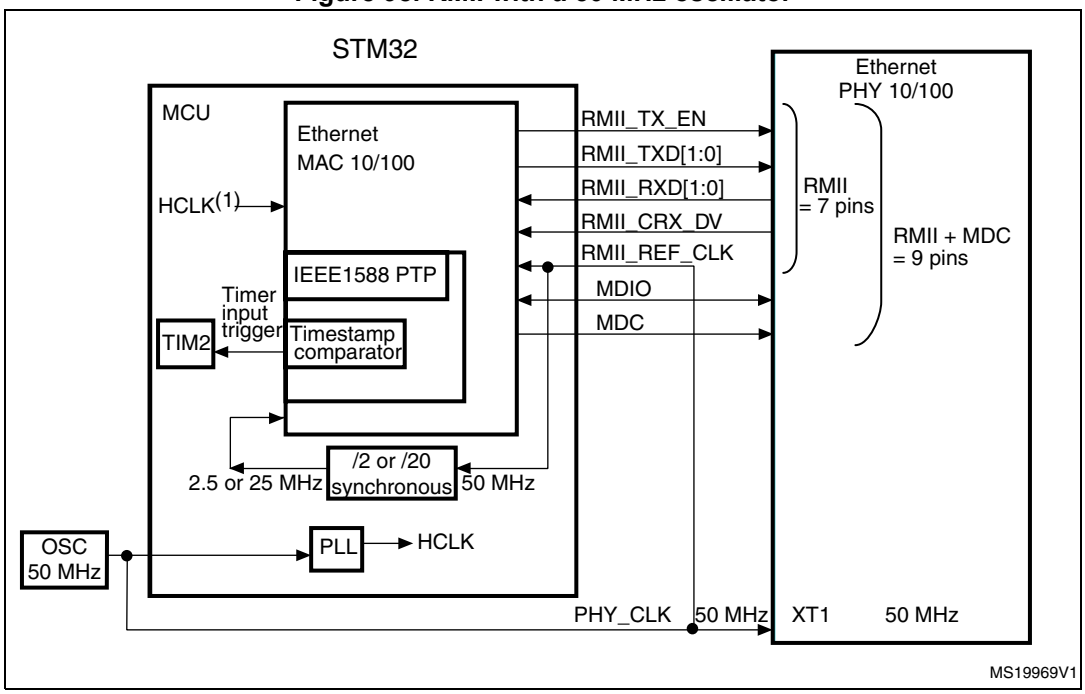
A.3 Ethernet interface solutions

Figure 97. MII mode using a 25 MHz crystal



1. f_{HCLK} must be greater than 25 MHz.
2. Pulse per second when using IEEE1588 PTP optional signal.

Figure 98. RMII with a 50 MHz oscillator



1. f_{HCLK} must be greater than 25 MHz.

Table 100. Document revision history (continued)

Date	Revision	Changes
24-Jan-2012	2 (continued)	Added V_{12} in *Table 19: Embedded reset and power control block characteristics*. Updated *Table 21: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator disabled)* and *Table 20: Typical and maximum current consumption in Run mode, code with data processing running from Flash memory (ART accelerator enabled) or RAM*. Added *Figure* , *Figure 25*, *Figure 26*, and *Figure 27*. Updated *Table 22: Typical and maximum current consumption in Sleep mode* and removed Note 1. Updated *Table 23: Typical and maximum current consumptions in Stop mode* and *Table 24: Typical and maximum current consumptions in Standby mode*, *Table 25: Typical and maximum current consumptions in VBAT mode*, and *Table 27: Switching output I/O current consumption*. *Section : On-chip peripheral current consumption*: modified conditions, and updated *Table 28: Peripheral current consumption* and *Note 2*. Changed f_{HSE_ext} to 50 MHz and $t_{r(HSE)}/t_{f(HSE)}$ maximum value in *Table 30: High-speed external user clock characteristics*. Added $C_{in(LSE)}$ in *Table 31: Low-speed external user clock characteristics*. Updated maximum PLL input clock frequency, removed related note, and deleted jitter for MCO for RMII Ethernet typical value in *Table 36: Main PLL characteristics*. Updated maximum PLLI2S input clock frequency and removed related note in *Table 37: PLLI2S (audio PLL) characteristics*. Updated *Section : Flash memory* to specify that the devices are shipped to customers with the Flash memory erased. Updated *Table 39: Flash memory characteristics*, and added t_{ME} in *Table 40: Flash memory programming*. Updated *Table 43: EMS characteristics*, and *Table 44: EMI characteristics*. Updated *Table 56: I2S dynamic characteristics* Updated *Figure 45: ULPI timing diagram* and *Table 62: ULPI timing*. Added $t_{COUNTER}$ and t_{MAX_COUNT} in *Table 52: Characteristics of TIMx connected to the APB1 domain* and *Table 53: Characteristics of TIMx connected to the APB2 domain*. Updated *Table 65: Dynamic characteristics: Ethernet MAC signals for RMII*. Removed USB-IF certification in *Section : USB OTG FS characteristics*.

Table 100. Document revision history (continued)

Date	Revision	Changes
04-Jun-2013	4 (continued)	Updated *Figure 6: Multi-AHB matrix*. Updated *Figure 7: Power supply supervisor interconnection with internal reset OFF* Changed 1.2 V to V_{12} in *Section : Regulator OFF* Updated LQFP176 pin 48. Updated *Section 1: Introduction*. Updated *Section 2: Description*. Updated operating voltage in *Table 2: STM32F405xx and STM32F407xx: features and peripheral counts*. Updated *Note 1*. Updated *Section 2.2.15: Power supply supervisor*. Updated *Section 2.2.16: Voltage regulator*. Updated *Figure 9: Regulator OFF*. Updated *Table 3: Regulator ON/OFF and internal reset ON/OFF availability*. Updated *Section 2.2.19: Low-power modes*. Updated *Section 2.2.20: VBAT operation*. Updated *Section 2.2.22: Inter-integrated circuit interface (I²C)* . Updated pin 48 in *Figure 15: STM32F40xxx LQFP176 pinout*. Updated *Table 6: Legend/abbreviations used in the pinout table*. Updated *Table 7: STM32F40xxx pin and ball definitions*. Updated *Table 14: General operating conditions*. Updated *Table 15: Limitations depending on the operating power supply range*. Updated *Section 5.3.7: Wakeup time from low-power mode*. Updated *Table 34: HSI oscillator characteristics*. Updated *Section 5.3.15: I/O current injection characteristics*. Updated *Table 48: I/O static characteristics*. Updated *Table 51: NRST pin characteristics*. Updated *Table 56: I^2C characteristics*. Updated *Figure 39: I^2C bus AC waveforms and measurement circuit*. Updated *Section 5.3.19: Communications interfaces*. Updated *Table 67: ADC characteristics*. Added *Table 70: Temperature sensor calibration values*. Added *Table 73: Internal reference voltage calibration values*. Updated *Section 5.3.26: FSMC characteristics*. Updated *Section 5.3.28: SD/SDIO MMC card host interface (SDIO) characteristics*. Updated *Table 23: Typical and maximum current consumptions in Stop mode*. Updated *Section : SPI interface characteristics* included *Table 55*. Updated *Section : I2S interface characteristics* included *Table 56*. Updated *Table 64: Dynamic characteristics: Eternity MAC signals for SMI*. Updated *Table 66: Dynamic characteristics: Ethernet MAC signals for MII*.